

ABSTRACT OF THE DISCLOSURE

The light-receiving surface of a photodiode is covered with a gate oxide film. Through the gate oxide film is formed an opening exposing a central region of the light-receiving surface of the photodiode. The formation of the opening is followed by forming an antireflection film formed of silicon nitride film, which covers the light-receiving surface of the photodiode, exposed from the opening; which has an end on a field oxide film side riding upon the gate oxide film, and reaching the position spaced by a predetermined distance away from a field oxide film that is adjacent to the photodiode; and which has an end on a transfer gate side riding upon the top of the gate oxide film located in the vicinity of the opening, and reaching up to the position spaced by a predetermined distance away from a gate electrode that is adjacent to the photodiode.